

UNR121x Series (UN121x Series)

Silicon NPN epitaxial planar type

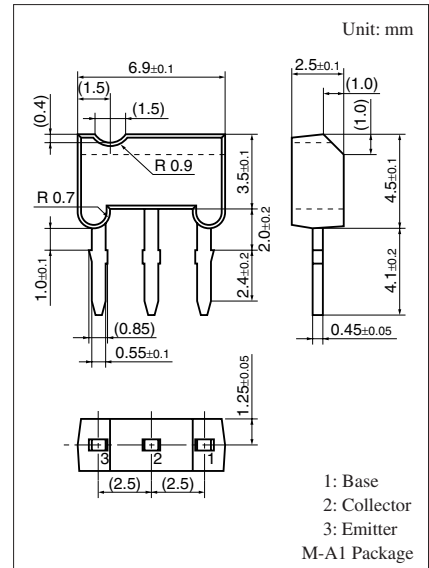
For digital circuits

■ Features

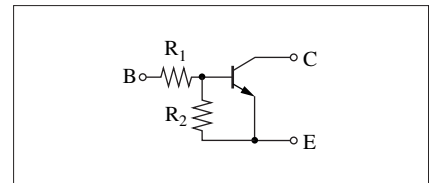
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board

■ Resistance by Part Number

	(R ₁)	(R ₂)
• UNR1210 (UN1210)	47 kΩ	—
• UNR1211 (UN1211)	10 kΩ	10 kΩ
• UNR1212 (UN1212)	22 kΩ	22 kΩ
• UNR1213 (UN1213)	47 kΩ	47 kΩ
• UNR1214 (UN1214)	10 kΩ	47 kΩ
• UNR1215 (UN1215)	10 kΩ	—
• UNR1216 (UN1216)	4.7 kΩ	—
• UNR1217 (UN1217)	22 kΩ	—
• UNR1218 (UN1218)	0.51 kΩ	5.1 kΩ
• UNR1219 (UN1219)	1 kΩ	10 kΩ
• UNR121D (UN121D)	47 kΩ	10 kΩ
• UNR121E (UN121E)	47 kΩ	22 kΩ
• UNR121F (UN121F)	4.7 kΩ	10 kΩ
• UNR121K (UN121K)	10 kΩ	4.7 kΩ
• UNR121L (UN121L)	4.7 kΩ	4.7 kΩ



Internal Connection



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■ Absolute Maximum Ratings T_a = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	50	V
Collector-emitter voltage (Base open)	V _{CEO}	50	V
Collector current	I _C	100	mA
Total power dissipation	P _T	400	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Note) The part numbers in the parenthesis show conventional part number.

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

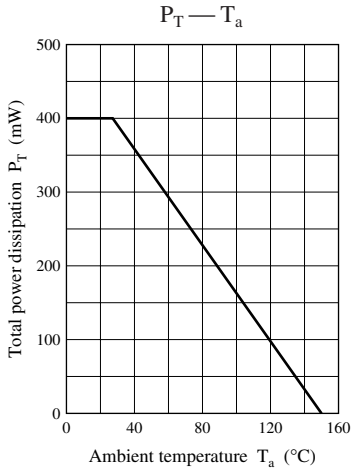
Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10 \mu\text{A}, I_E = 0$	50			V	
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 2 \text{ mA}, I_B = 0$	50			V	
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	μA	
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 50 \text{ V}, I_B = 0$			0.5	μA	
Emitter-base cutoff current (Collector open)	UNR1211	I_{EBO}	$V_{EB} = 6 \text{ V}, I_C = 0$			0.5	mA
	UNR1212/1214/121D/121E					0.2	
	UNR1213					0.1	
	UNR1210/1215/1216/1217					0.01	
	UNR121F/121K					1.0	
	UNR1219					1.5	
	UNR1218/121L					2.0	
Forward current transfer ratio	UNR1211	h_{FE}	$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$	35			—
	UNR1212/121E			60			
	UNR1213/1214			80			
	UNR1210*/1215*/1216*/1217*			160		460	
	UNR1219/121D/121F			30			
	UNR1218/121K/121L			20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$			0.25	V	
Output voltage high-level	V_{OH}	$V_{CC} = 5 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	4.9			V	
Output voltage low-level	V_{OL}	$V_{CC} = 5 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1 \text{ k}\Omega$			0.2	V	
		$V_{CC} = 5 \text{ V}, V_B = 3.5 \text{ V}, R_L = 1 \text{ k}\Omega$					
		$V_{CC} = 5 \text{ V}, V_B = 10 \text{ V}, R_L = 1 \text{ k}\Omega$					
		$V_{CC} = 5 \text{ V}, V_B = 6 \text{ V}, R_L = 1 \text{ k}\Omega$					
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		80		MHz	
Input resistance	UNR1211/1214/1215/121K	R_1		-30%	10	+30%	k Ω
	UNR1212/1217				22		
	UNR1210/1213/121D/121E				47		
	UNR1216/121F/121L				4.7		
	UNR1218				0.51		
	UNR1219				1		
Resistance ratio	UNR1211/1212/1213/121L	R_1/R_2		0.8	1.0	1.2	—
	UNR1214			0.17	0.21	0.25	
	UNR1218/1219			0.08	0.1	0.12	
	UNR121D				4.7		
	UNR121E				2.14		
	UNR121F				0.47		
	UNR121K				2.13		

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

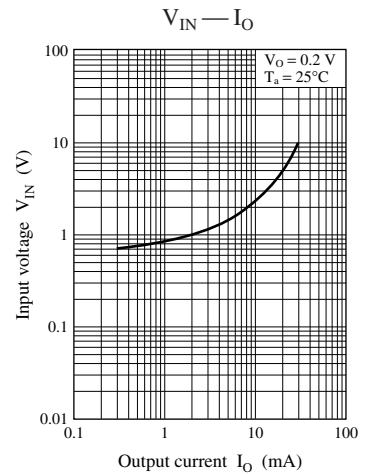
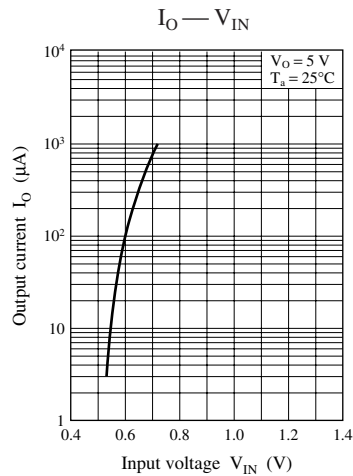
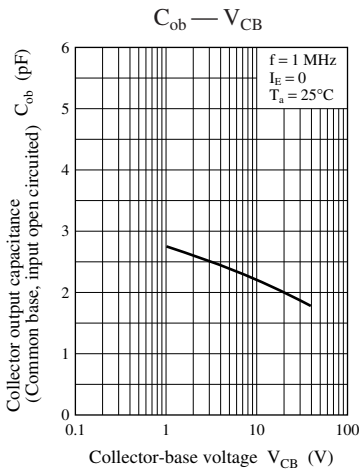
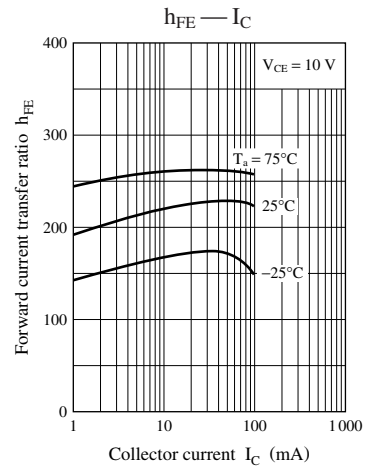
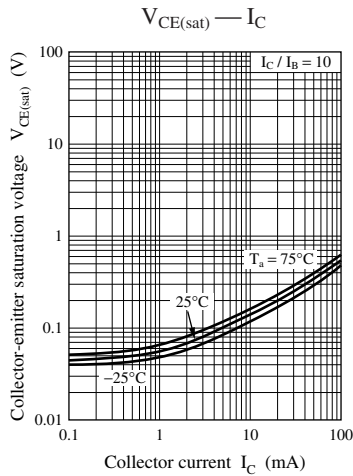
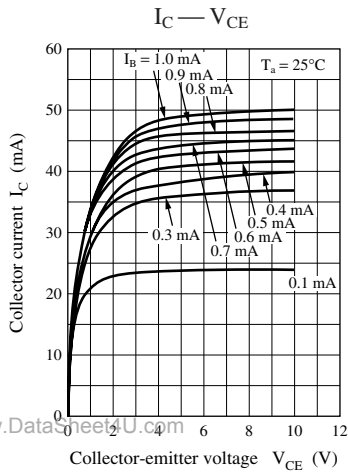
2. *: Rank classification (UNR1110/1115/1116/1117)

Rank	Q	R	S
h_{FE}	160 to 260	210 to 340	290 to 460

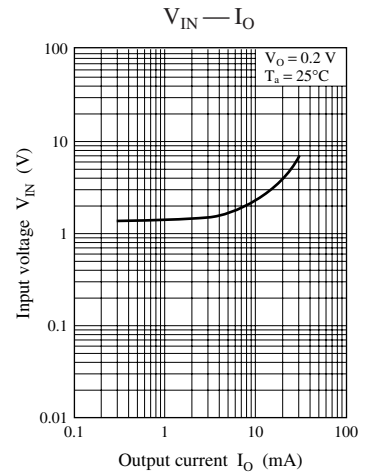
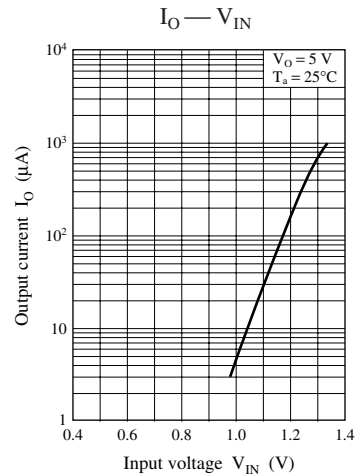
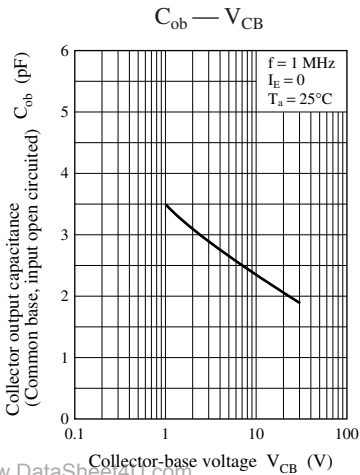
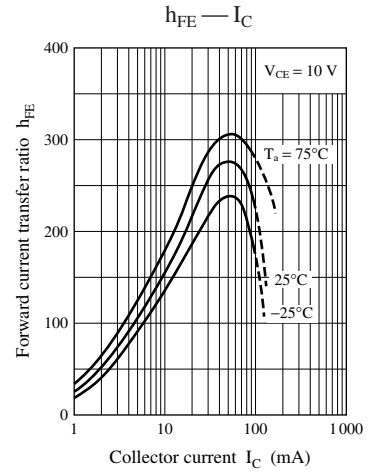
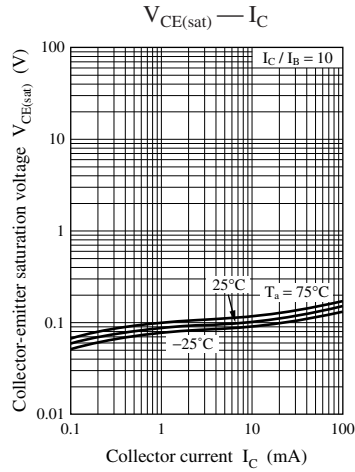
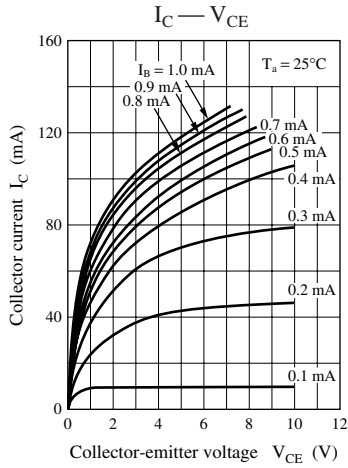
Common characteristics chart



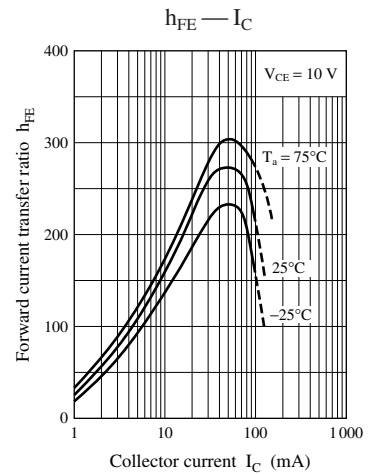
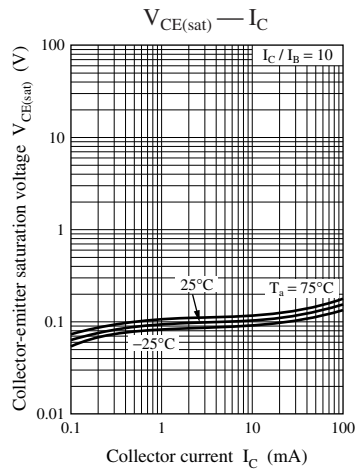
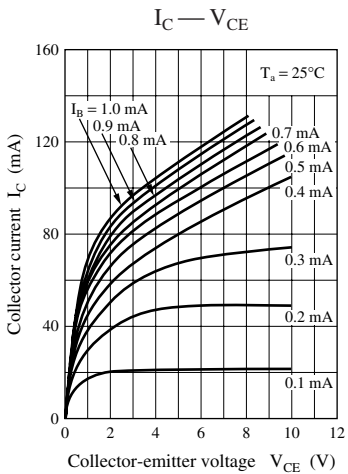
Characteristics charts of UNR1210

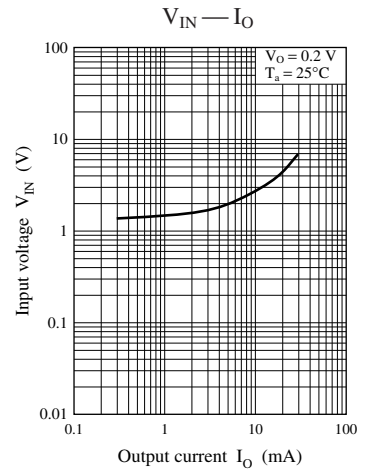
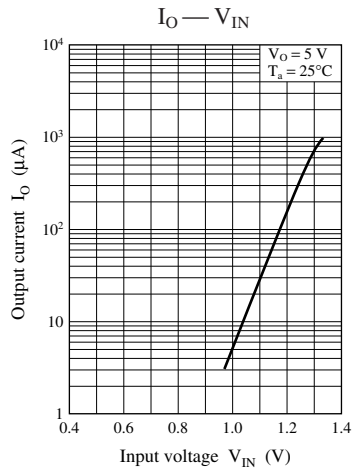
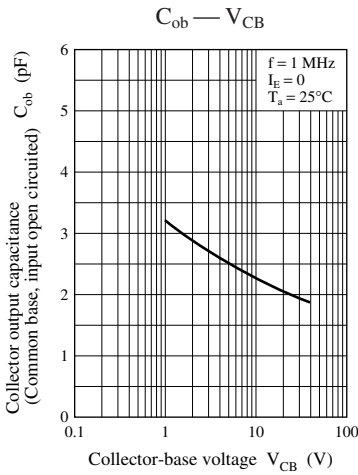


Characteristics charts of UNR1211

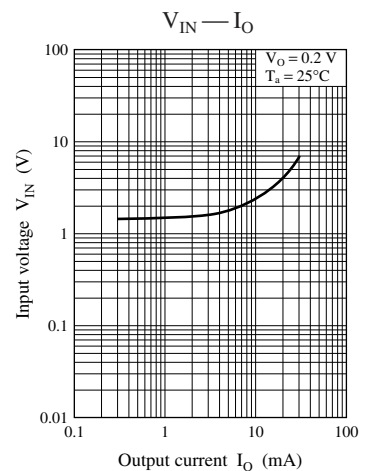
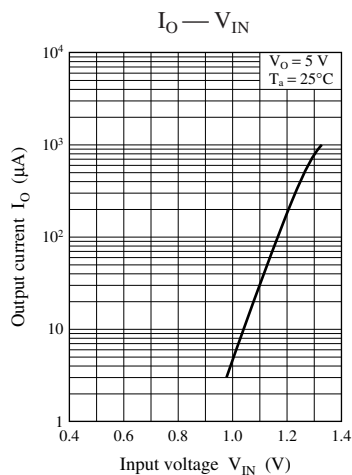
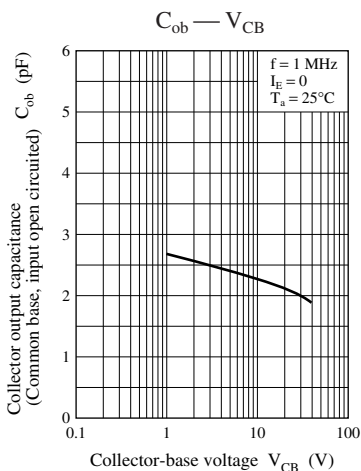
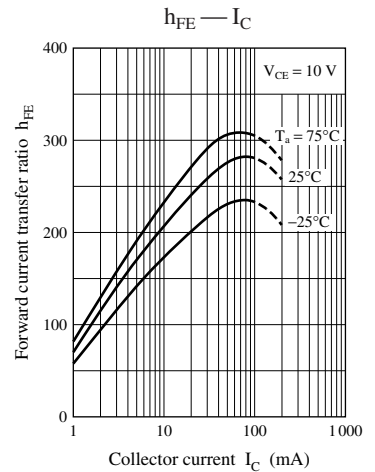
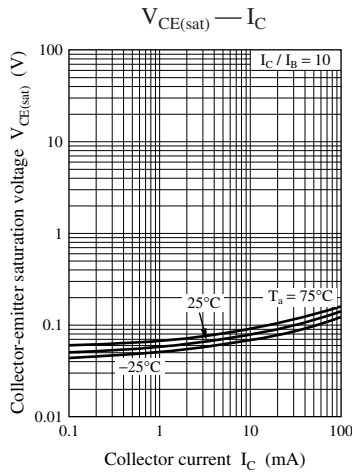
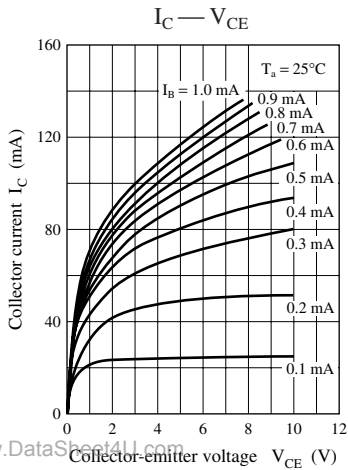


Characteristics charts of UNR1212

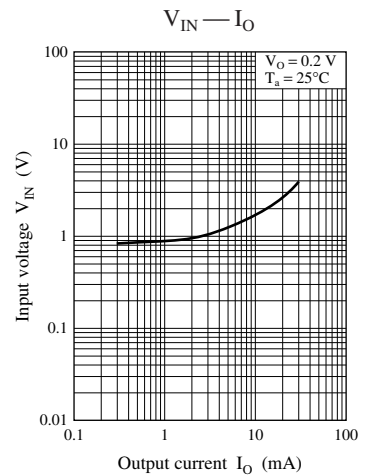
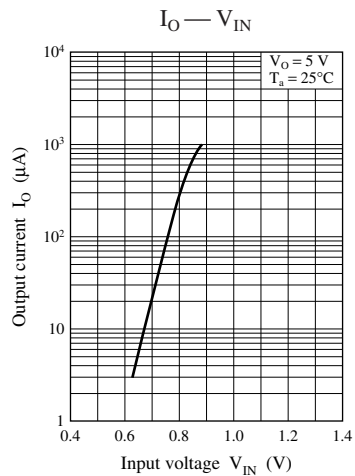
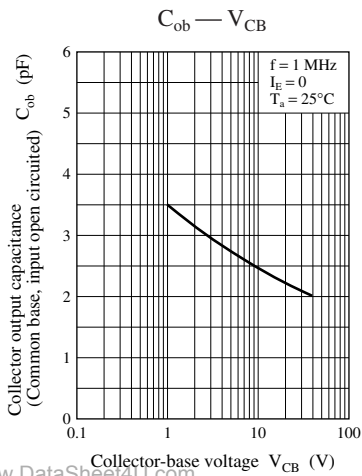
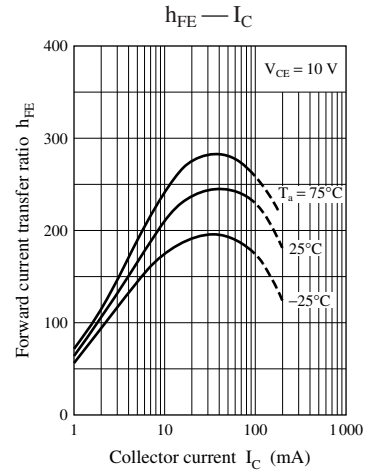
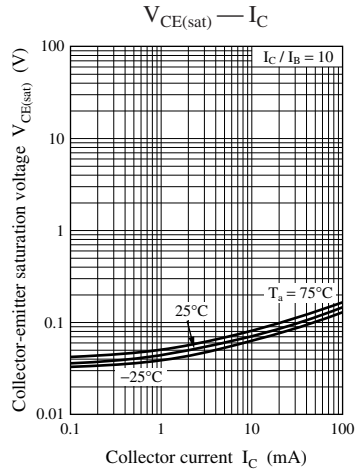
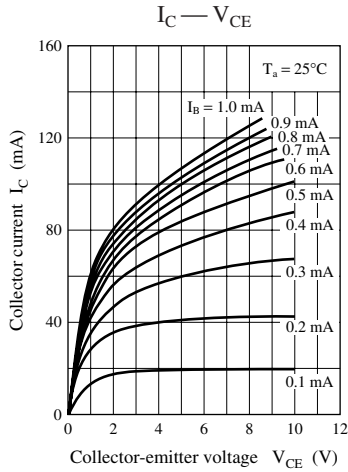




Characteristics charts of UNR1213

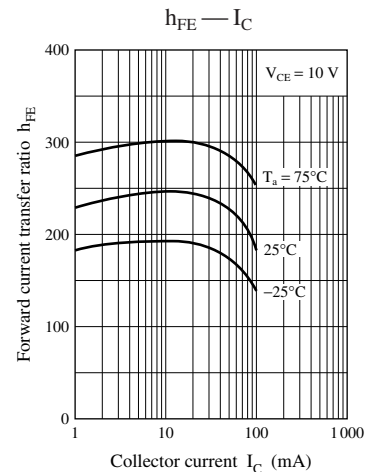
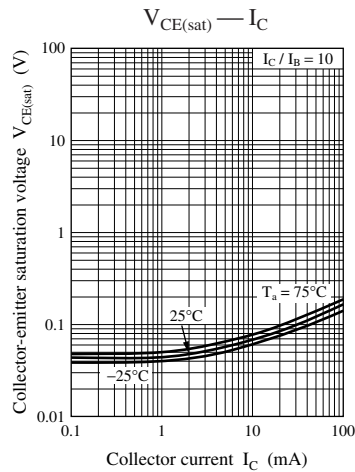
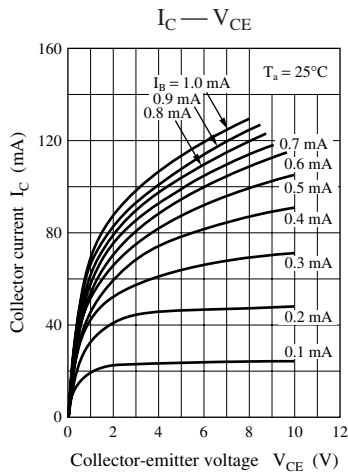


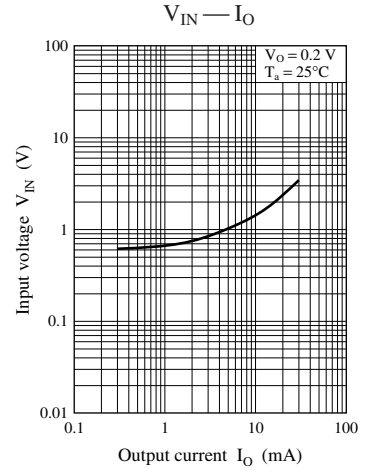
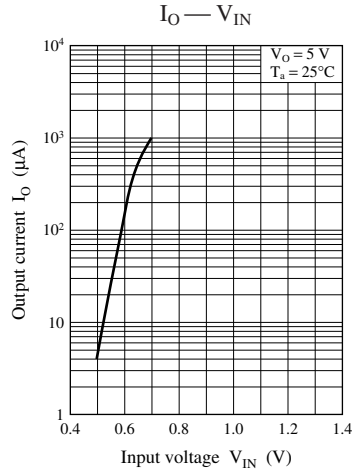
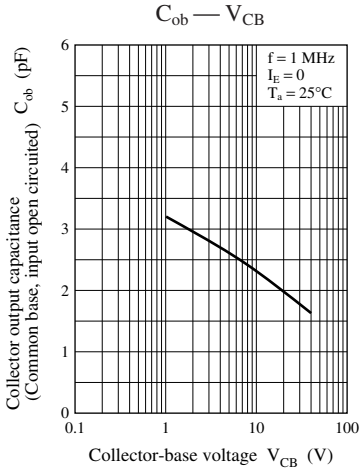
Characteristics charts of UNR1214



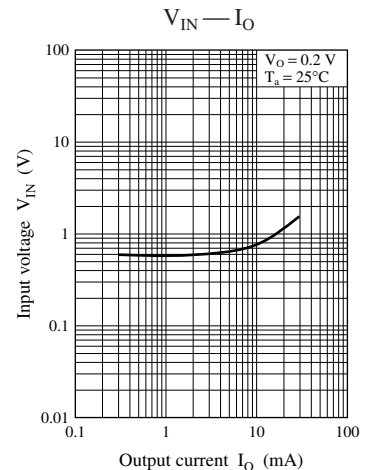
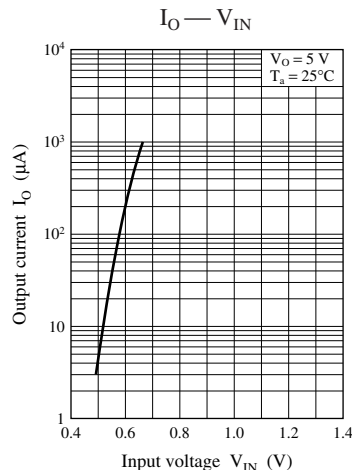
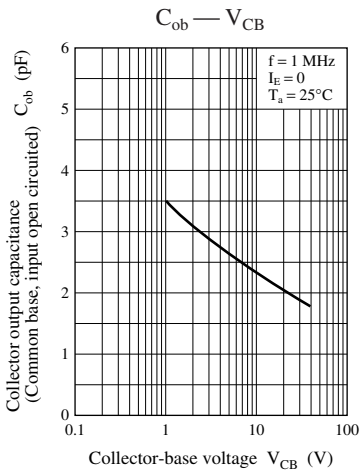
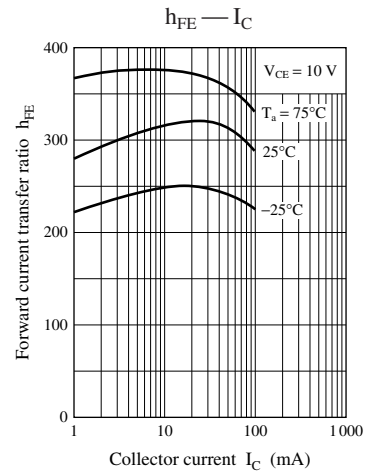
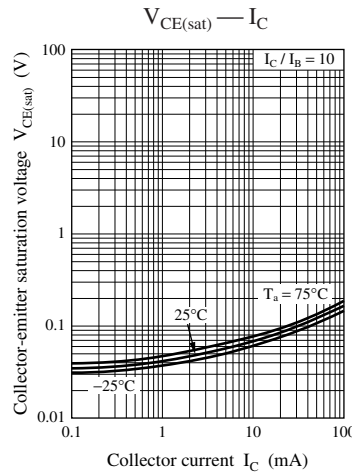
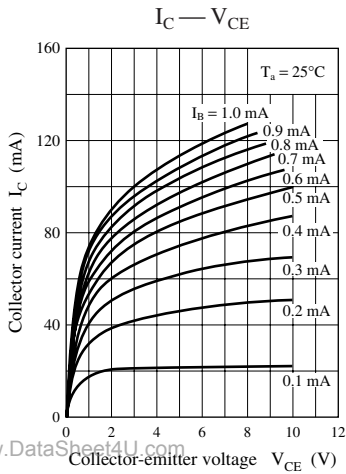
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Characteristics charts of UNR1215

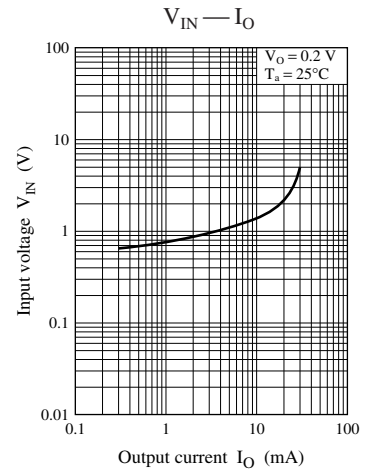
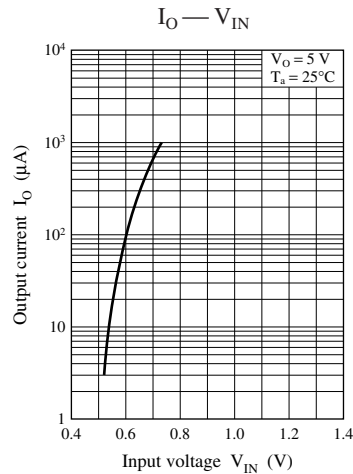
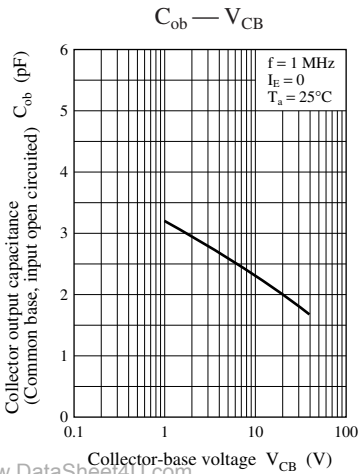
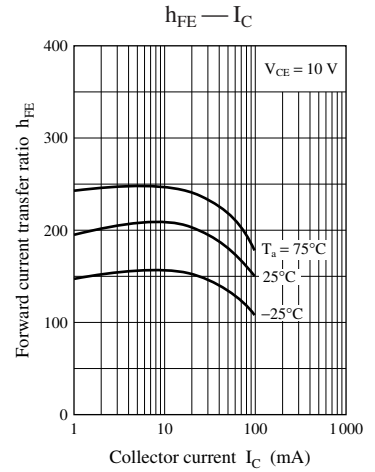
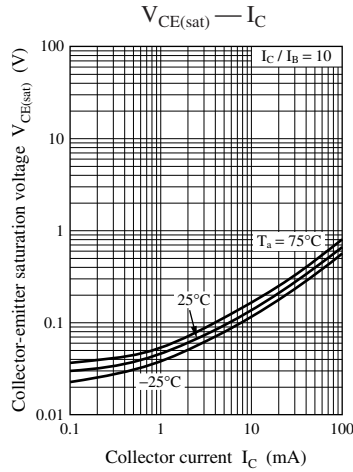
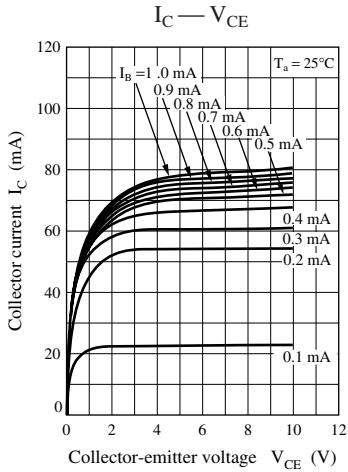




Characteristics charts of UNR1216

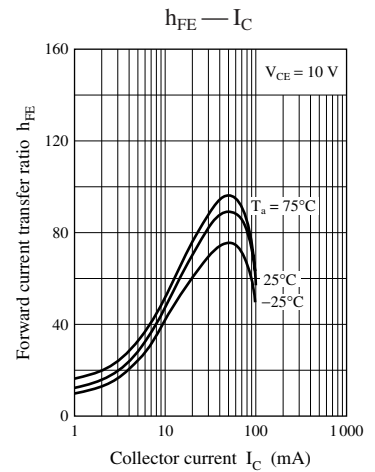
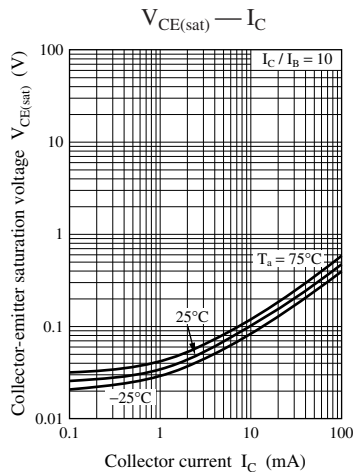
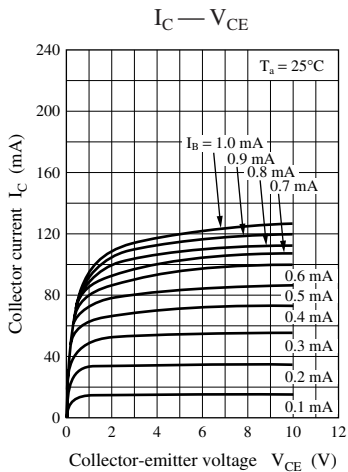


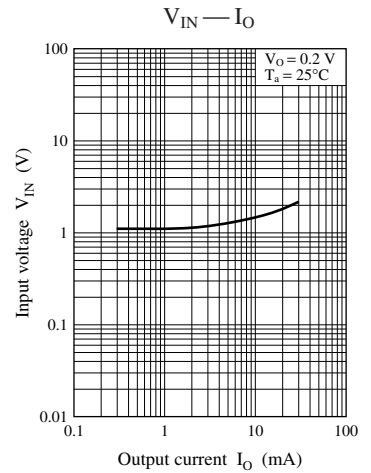
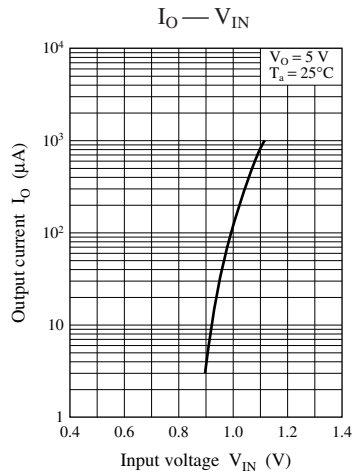
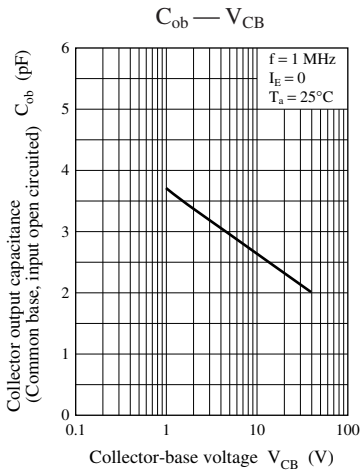
Characteristics charts of UNR1217



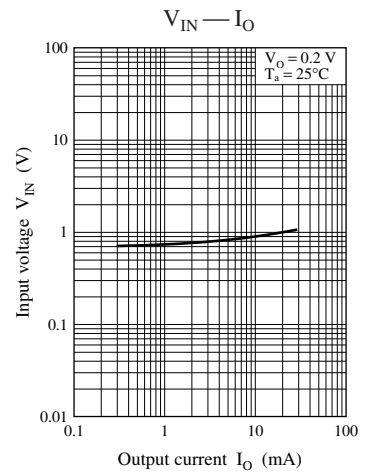
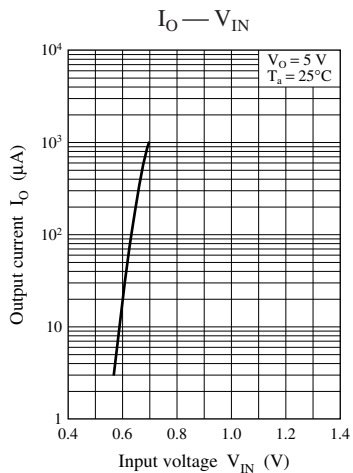
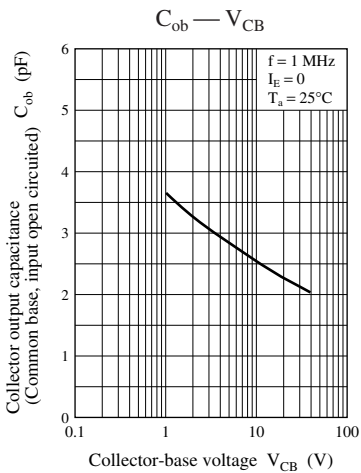
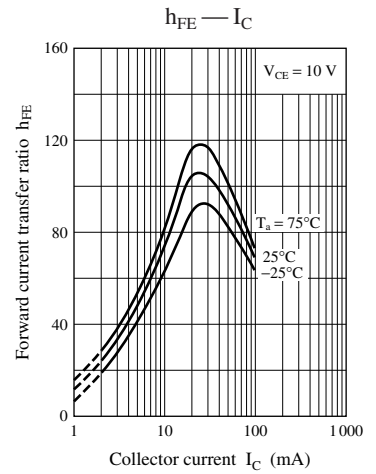
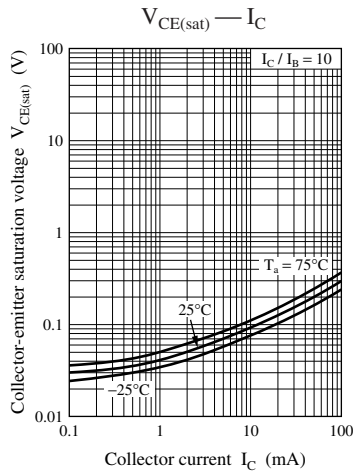
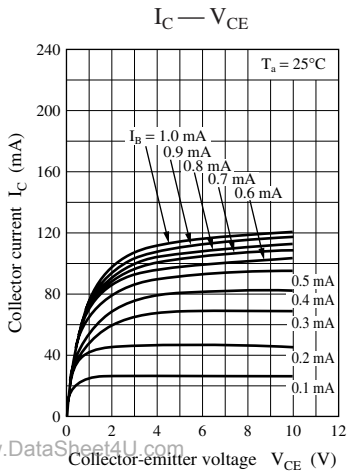
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Characteristics charts of UNR1218

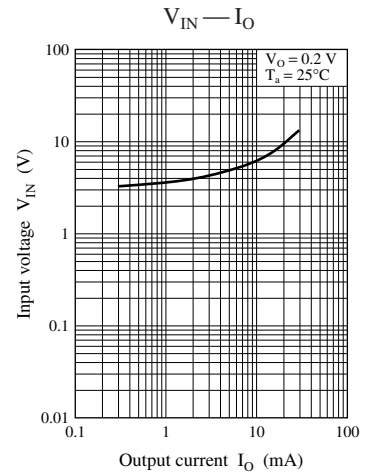
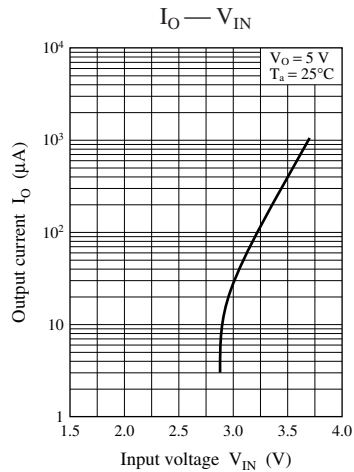
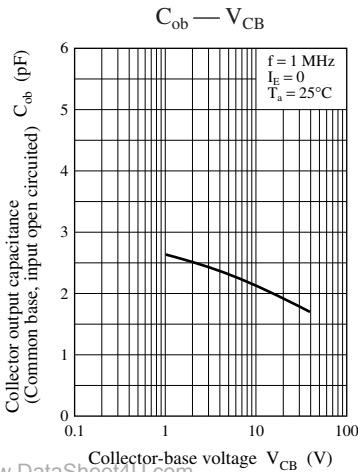
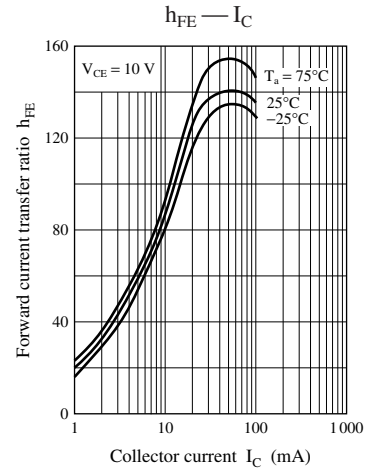
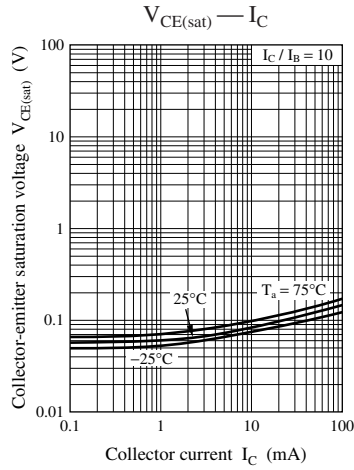
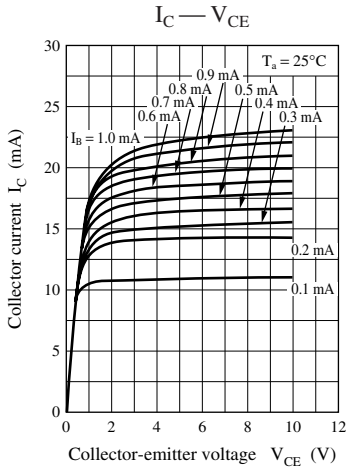




Characteristics charts of UNR1219

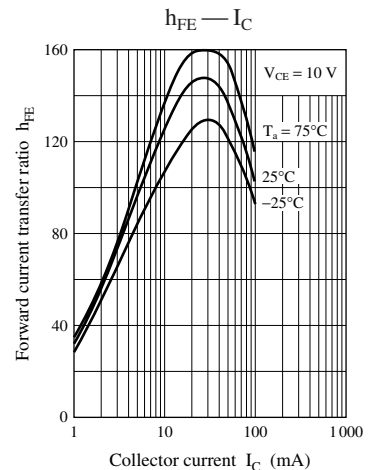
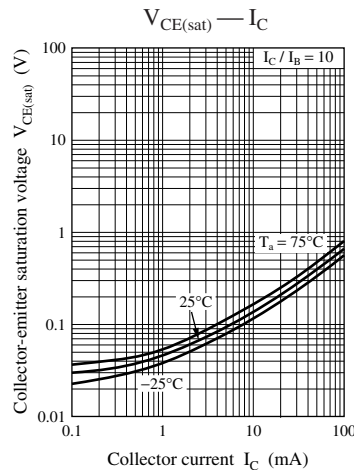
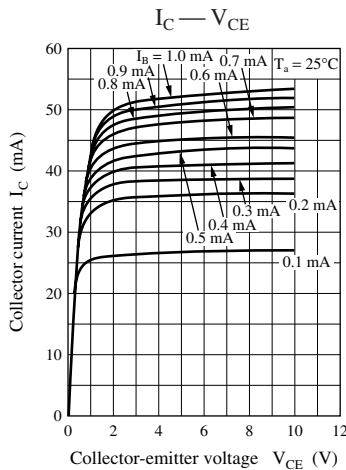


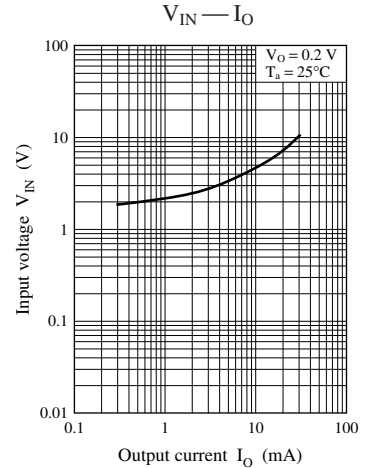
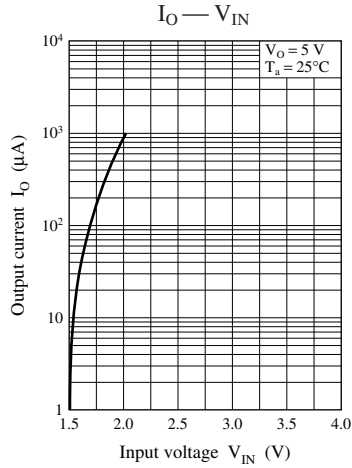
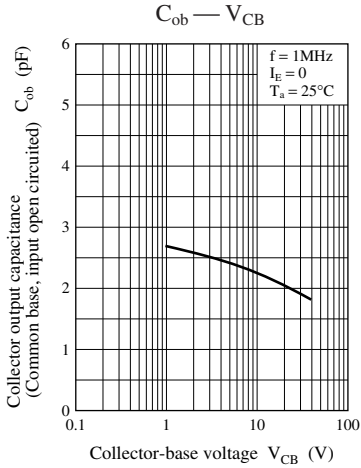
Characteristics charts of UNR121D



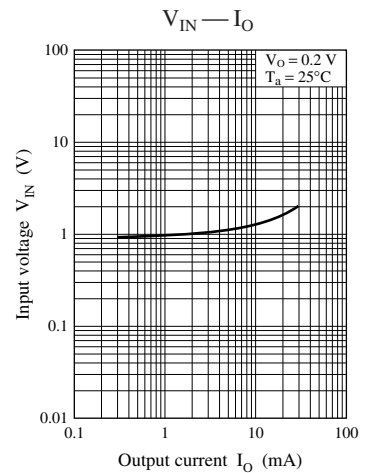
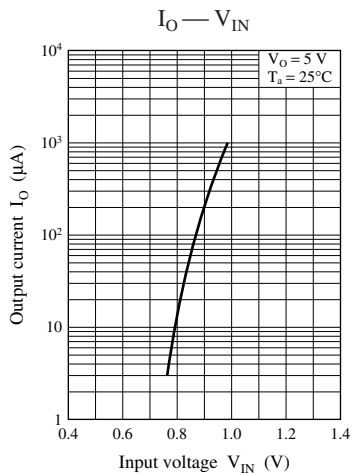
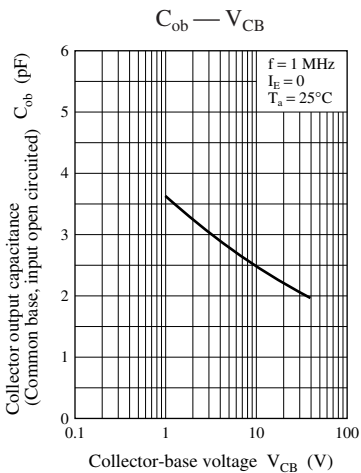
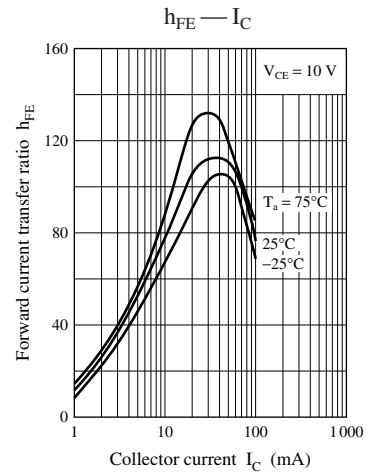
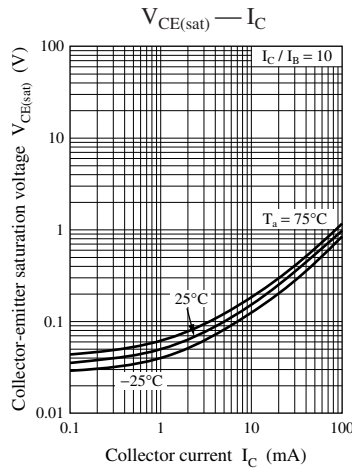
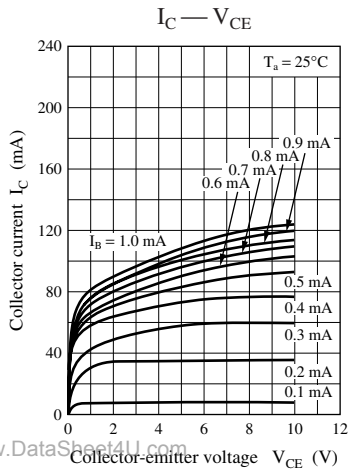
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Characteristics charts of UNR121E

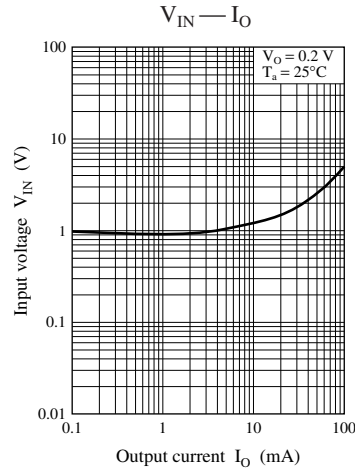
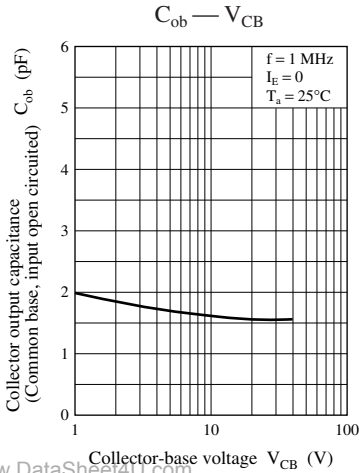
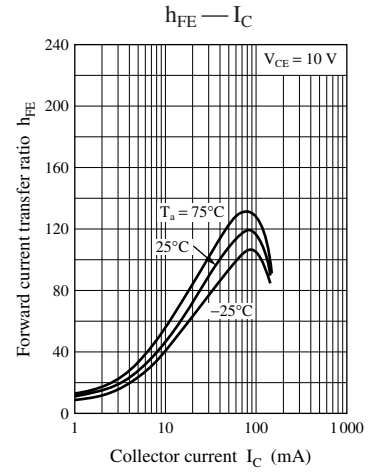
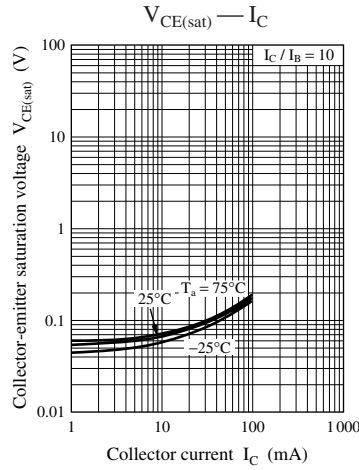
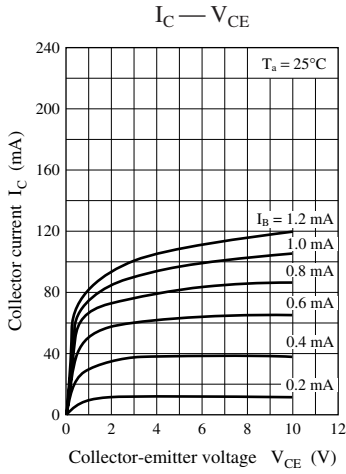




Characteristics charts of UNR121F

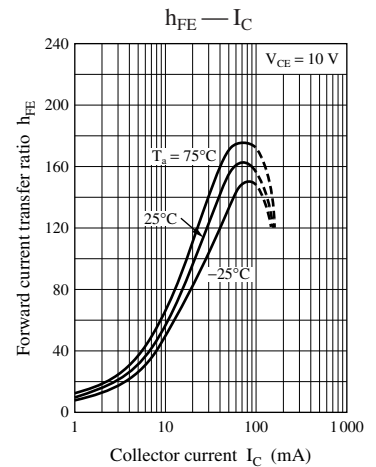
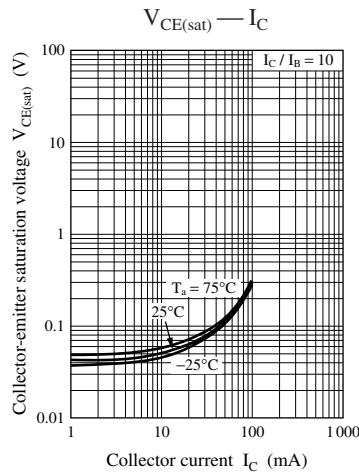
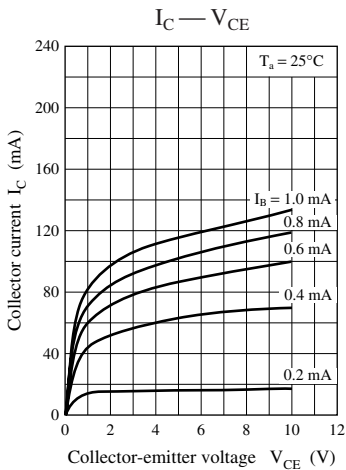


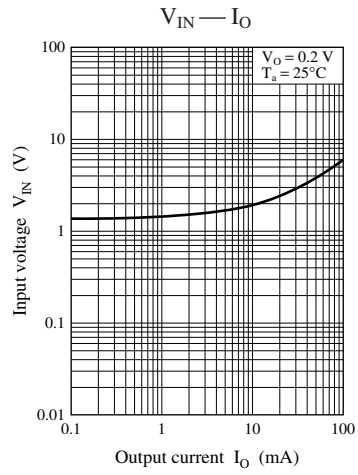
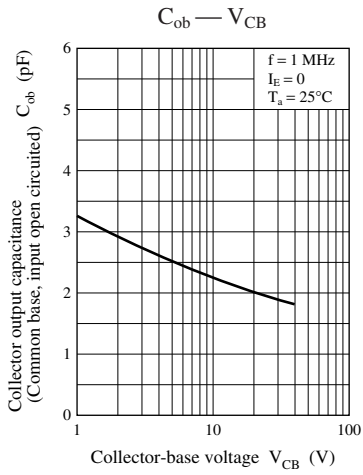
Characteristics charts of UNR121K



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Characteristics charts of UNR121L





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